

PMBTA45

500 V, 150 mA NPN high-voltage low VCEsat transistor 20 July 2023 Product data sheet

1. General description

NPN high-voltage low V_{CEsat} transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package.

PNP complement: PBHV9050T

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- AEC-Q101 qualified

3. Applications

- Electronic ballasts
- · LED driver for LED chain module
- LCD backlighting
- Automotive motor management
- Flyback converters
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	500	V
V _{CEO}	collector-emitter voltage	open base	-	-	500	V
I _C	collector current		-	-	0.15	Α
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 30 mA; T _{amb} = 25 °C	50	100	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		j
3	С	collector		В —
				 E
			1	sym021

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMBTA45		plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PMBTA45	LK%

^{[1] % =} placeholder for manufacturing site code

8. Limiting values

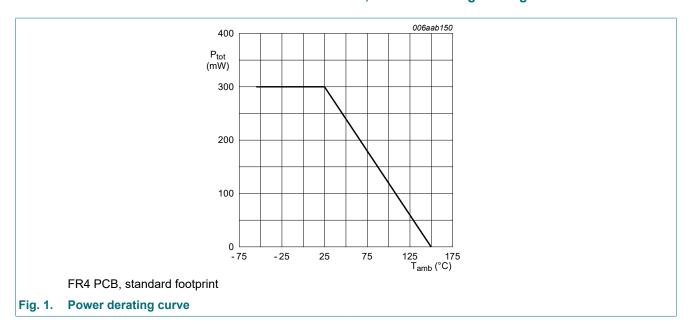
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	500	V
V _{CEO}	collector-emitter voltage	open base		-	500	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	500	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	0.15	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	0.5	Α
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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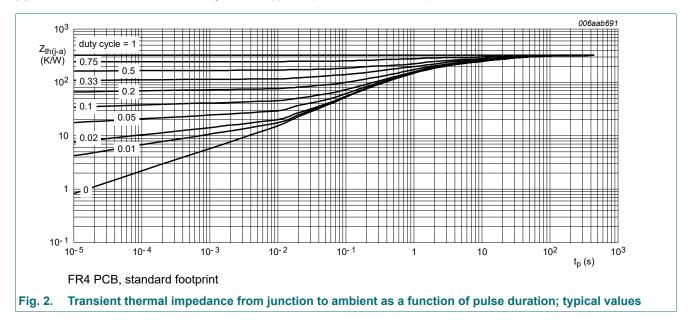


9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	70	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 360 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
cur	current	V _{CB} = 360 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
I _{CES}	collector-emitter cut-off current	V _{CE} = 360 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 10 V; I _C = 30 mA; T _{amb} = 25 °C	50	100	-	
		V_{CE} = 10 V; I_{C} = 50 mA; pulsed; t_{p} ≤ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	50	100	-	
V _{CEsat}	CEsat collector-emitter saturation voltage	I_C = 20 mA; I_B = 2 mA; T_{amb} = 25 °C	-	60	75	mV
		I_C = 50 mA; I_B = 6 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	65	90	mV
V _{BEsat}	base-emitter saturation voltage	I_C = 50 mA; I_B = 5 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	0.75	0.9	V
t _d	delay time	V _{CC} = 20 V; I _C = 0.05 A; I _{Bon} = 5 mA;	-	80	-	ns
t _r	rise time	I _{Boff} = -10 mA; T _{amb} = 25 °C	-	2700	-	ns
t _{on}	turn-on time		-	2780	-	ns
t _s	storage time		-	3400	-	ns
t _f	fall time		-	800	-	ns
t _{off}	turn-off time		-	4200	-	ns
f _T	transition frequency	V_{CE} = 10 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C	-	35	-	MHz
C _c	collector capacitance	V_{CB} = 20 V; I_{E} = 0 A; i_{e} = 0 A; f = 1 MHz; T_{amb} = 25 °C	-	4	-	pF
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 ^{\circ}\text{C}$	-	200	-	pF

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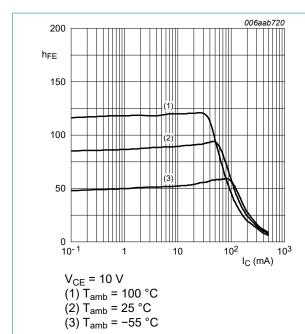


Fig. 3. DC current gain as a function of collector current; typical values

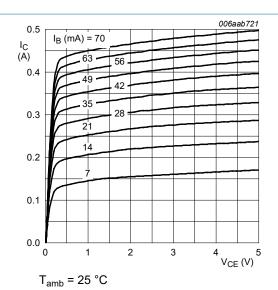
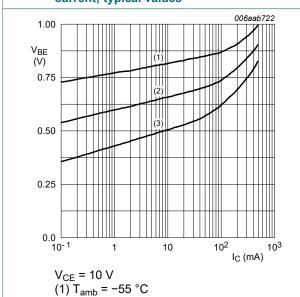


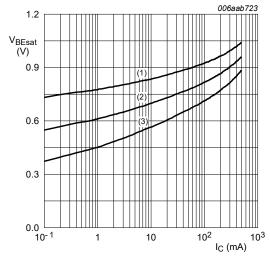
Fig. 4. Collector current as a function of collectoremitter voltage; typical values



(3) T_{amb} = 100 °C Fig. 5. Base-emitter voltage as a function of collector

current; typical values

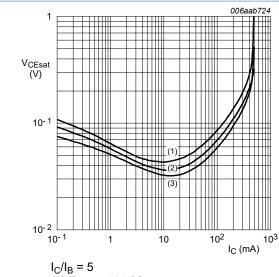
(2) T_{amb} = 25 °C



 $I_{\rm C}/I_{\rm B} = 5$ (1) $T_{\rm amb} = -55~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = 100~{\rm ^{\circ}C}$

Fig. 6. Base-emitter saturation voltage as a function of collector current; typical values

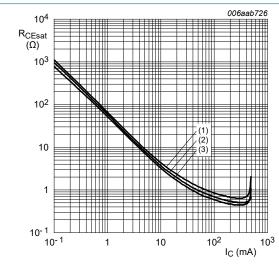
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$$^{1}C/^{1}B - 3$$

(1) $T_{amb} = 100 ^{\circ}C$
(2) $T_{amb} = 25 ^{\circ}C$
(3) $T_{amb} = -55 ^{\circ}C$

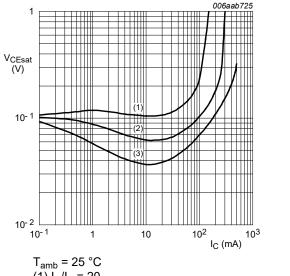
Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values



 $I_C/I_B = 5$ (1) T_{amb} = 100 °C (2) $T_{amb} = 25 \, ^{\circ}C$

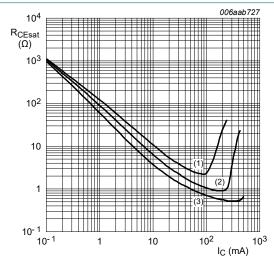
(3) $T_{amb} = -55 \, ^{\circ}C$

Fig. 9. Collector-emitter saturation resistance as a function of collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$ (1) $I_C/I_B = 20$ $(2) I_{C}/I_{B} = 10$ (3) $I_C/I_B = 5$

Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

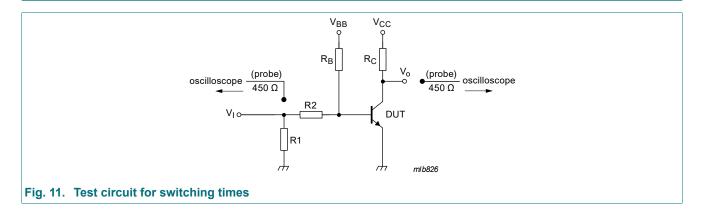


 T_{amb} = 25 °C $(1) I_{\rm C}/I_{\rm B} = 20$ $(2) I_{\rm C}/I_{\rm B} = 10$ (3) $I_C/I_B = 5$

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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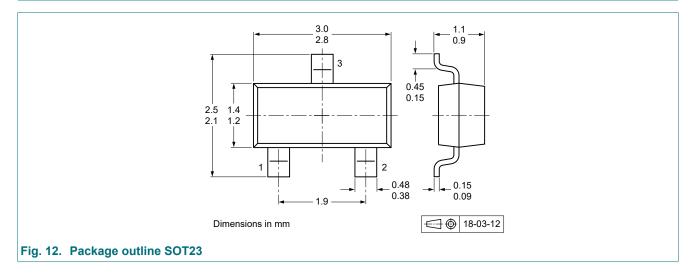
11. Test information



Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

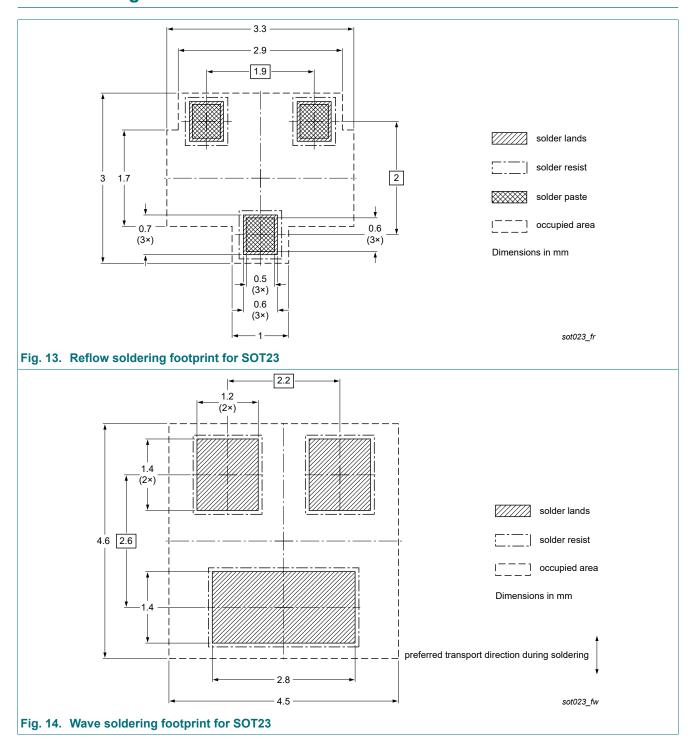
12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMBTA45 v.3	20230720	Product data sheet	-	PMBTA45_2		
Modifications:	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Section "Packing information" removed. 					
PMBTA45_2	20100310	Product data sheet	-	PMBTA45_1		
PMBTA45_1	20090916	Product data sheet	-	-		

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15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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- [2] The term 'short data sheet' is explained in section "Definitions".
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